Docket No.: 15675P568

MAY 23 2005

Application of:

BERNARD BEAUMONT, ET AL.

Application No.: 10/522,397

Filed: January 31, 2005

For: Method For Producing By Vapour-Phase

Epitaxy a Gallium Nitride Film With Low

**Defect Density** 

Art Group:

Examiner:

## INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08 or PTO-1449), together with copies of the documents cited on that form, except for copies not required to be submitted (e.g., copies of U.S. patents and U.S. published patent applications need not be enclosed), which are being submitted before the mailing of a first Office Action. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

The references were cited in a Search Report dated March 11, 2004 (copy enclosed herewith) in a counterpart EPO application, which was forwarded to Applicant's Representative in a communication dated March 18, 2004.

It is noted that the column labeled "Categorie" translates to Category, the column "Identification des documents cités, avec, le cas échéant, l'indication des passages pertinents" translates to citation for document with indication, where appropriate, of relevant passages and the column labeled "no, des revendications visées" translates to relevant to claims.

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Date: \_\_\_\_\_\_

Respectfully submitted,

Blakely, Soko**loff, T**aylor & Zafman LLP

Eric S. Hyman, Reg. No. 30,139

12400 Wilshire Boulevard, 7th Floor Los Angeles, CA 90025 Telephone: (310) 207-3800

I hereby certify that this correspondence is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Melissa Stead

Date

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Substitute for form 1449A/PTO

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 2

Comprete if Known				
Application Number	10/522,397			
Filing Date	January 31, 2005			
First Named Inventor	Bernard Beaumont			
Art Unit				
Examiner Name				
Attorney Docket Number	15675P568			

	U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.1	Document Number  Number - Kind Code <sup>2</sup> (if known)	Publication Date or Issue Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
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FOREIGN PATENT DOCUMENTS						
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		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)		Name of Patentee or Applicant of Cited Document		
/RK/		WO 99/20816	04-29-1999	Guillaune		
/RK/	I.	EP 1088914	04-04-2001	Sumitomo Electric Indust.		<u> </u>
7RK/	1	EP 0942459	09-15-1999	Nichia Chemical Industries, Ltd.		<u> </u>
/RK/		EP 1005068	05-31-2000	Sony Corp.		-
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<sup>\*</sup>Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

<sup>&</sup>lt;sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

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		Application Number	1 10/5

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 2 of 2

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Application Number 10/522,397			
Filing Date	January 31, 2005		
First Named Inventor	Bernard Beaumont		
Art Unit			
Examiner Name			
Attorney Docket Number	15675P568		

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²	
/RK/		"Reduction mechanisms for defect densities in GaN using one-or two-stop epitaxial lateral overgrowth methods", P. Vennegues, et al., Journal of applied Physics, Vol. 87. no. 9, 5/1/2000, pgs 4175-4181		
/RK/		"Fabrication and characterization of low defect density GaN using facet-controlled epitaxial later overgrowth (FACELO), Hiramatsu, et al., Journal of Crystal Growth, vol. 221, no. 1-4, pags 316-326		
/RK/		"Dislocation medicated surface morphology of GaN", B. Heying, Journal of Aplied Physics, vol. 85, no. 9, 5/1/1999, pgs 6470-6476		
/RK/		"Effect of SB as a Surfactant During the Lateral Epitaxial Overgrowth of Gan by Metalorganic Vapor Phas Epitaxy", Zhang et al, Applied Physics Letters, vol. 79, no. 19, 11/5/2001, pgs 3059-6951		

Examiner	/Robert Kunemund/	Date	06/25/2008
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